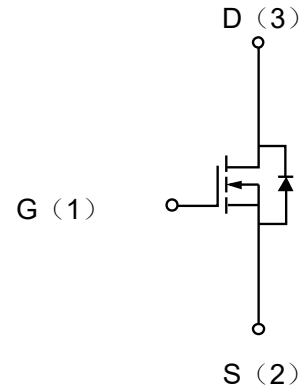


Description

The enhancement mode MOS is extremely high density cell and low on-resistance.

MOSFET Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(\Omega)$	$I_D(A)$
20	0.024@ $V_{GS}=4.5V$	5.5

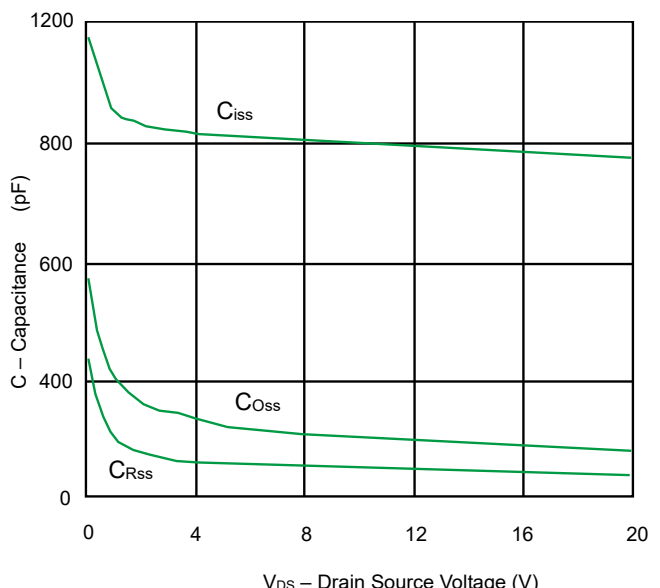
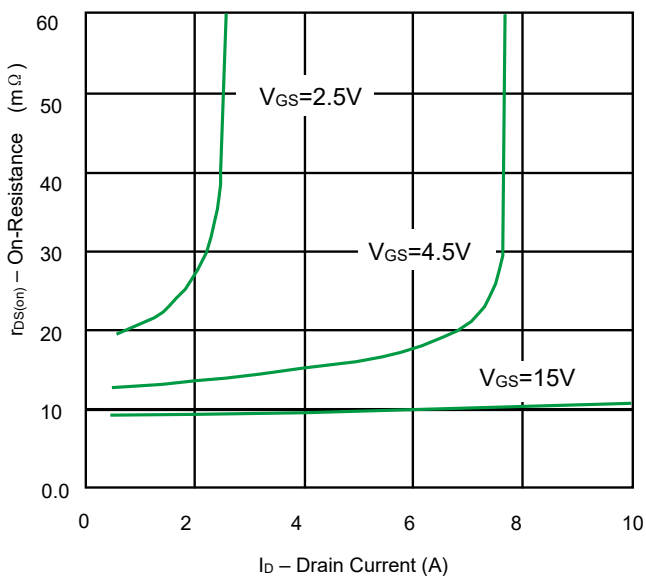
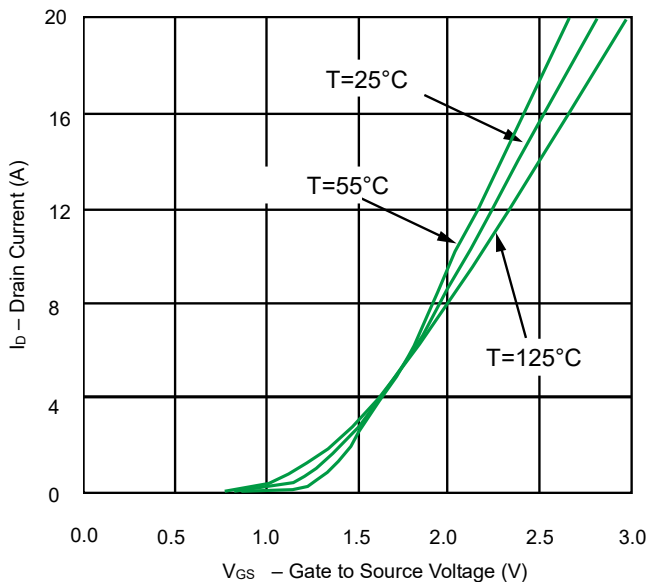
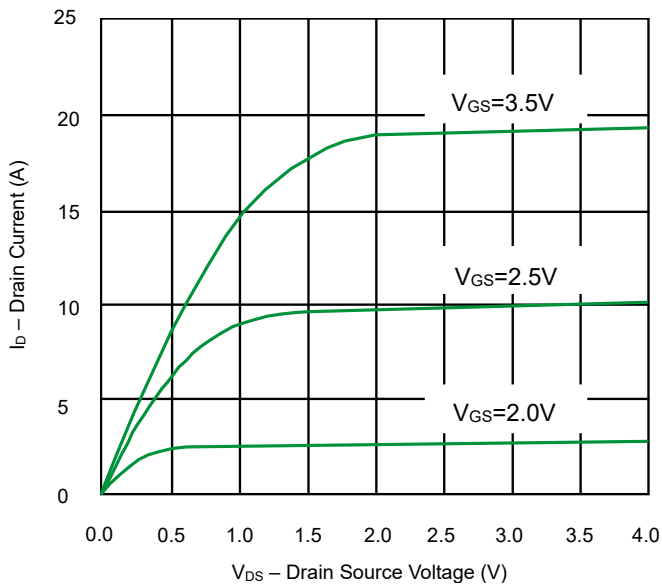

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	20		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 8V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5		1.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=4.5A$	-	0.024	0.028	Ω
		$V_{GS}=2.5V, I_D=2A$	-	0.030	0.037	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=15V,$ $f=1MHz$	-	520		pF
Output Capacitance	C_{OSS}		-	100		pF
Reverse Transfer Capacitance	C_{RSS}		-	80		pF
SWITCHING PARAMETERS						
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=10V, V_{GS}=4.5V,$ $R_G=10\Omega,$ $I_D=1A$	-		5	ns
Turn-Off Delay Time	$t_{d(off)}$		-		40	ns

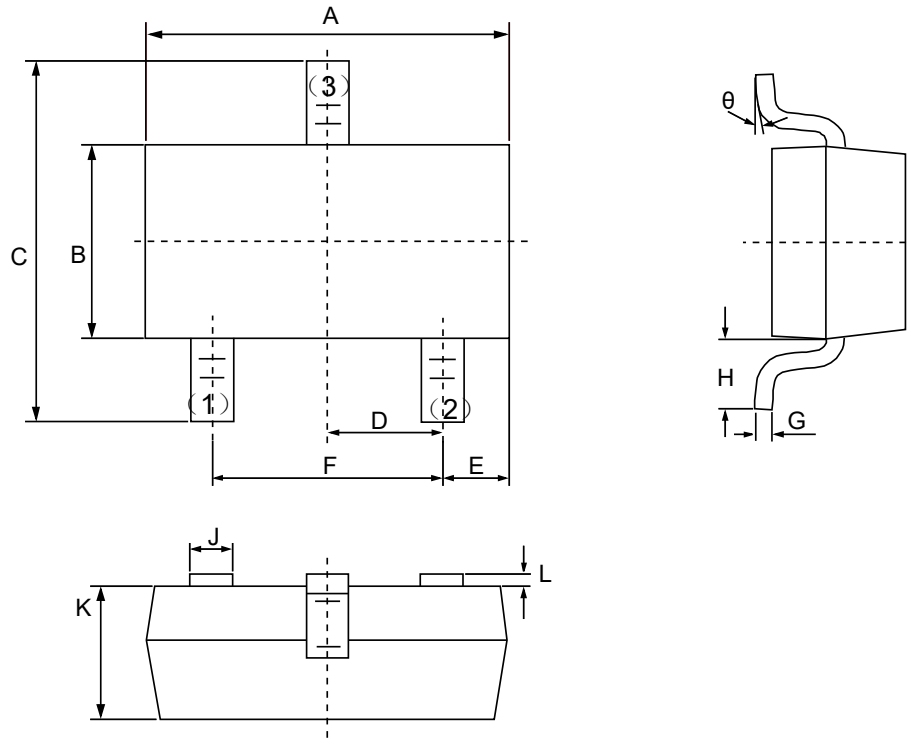
Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 10	V
Drain Current	Continuous	I_D	5.5	A
	Pulsed	I_D	28	A
Total Power Dissipation	$T_A=25^\circ\text{C}$	P_D	1.4	W
	$T_A=70^\circ\text{C}$	P_D	1	W

Typical Characteristics

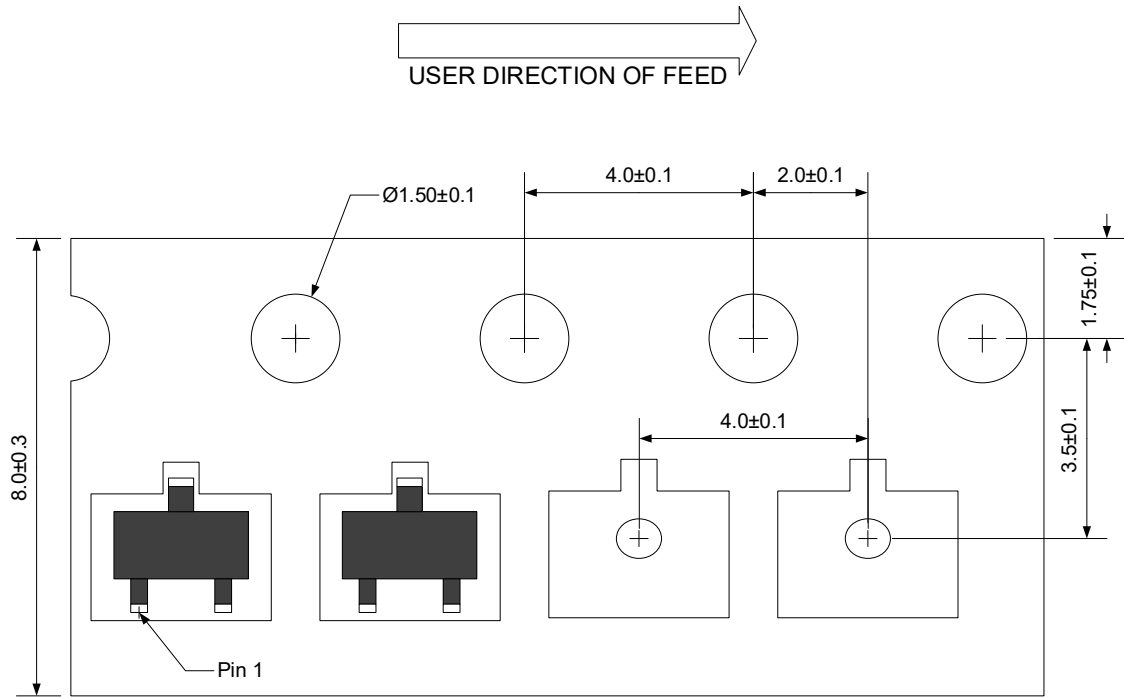


Product dimension(SOT-23)

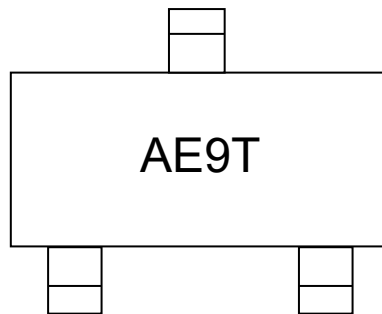


Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.80	3.00	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	2.10	2.50	0.0830	0.0984
D	0.89	1.02	0.0350	0.0401
E	0.45	0.60	0.0177	0.0236
F	1.78	2.04	0.0701	0.0807
G	0.085	0.177	0.0034	0.0070
H	0.45	0.60	0.0180	0.0236
J	0.37	0.50	0.0150	0.0200
K	0.89	1.11	0.0350	0.0440
L	0.013	0.100	0.0005	0.0040
θ	0°	10°	0°	10°


Load With Information



Marking Information




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